What is claimed is:

1. A method for fabricating a capacitor of a semiconductor device, comprising the steps of:

(a) forming a conductive silicon layer for a bottom electrode on a substrate;

(b) nitridating the conductive silicon layer;

(c) oxidizing the nitridated conductive silicon layer;

(d) forming a silicon nitride layer on a surface of the oxidized layer;

(e) forming a dielectric layer on the silicon nitride layer; and

(f) forming a top electrode on the dielectric layer.

2. The method as recited in claim 1, wherein at the step (c), a native oxide layer is used.

3. The method as recited in claim 2, wherein the native oxide layer is formed in a thickness ranging from about 1 Å to about 5 Å.

4. The method as recited in claim 3, wherein at the step (b), a thermal treatment process is carried out in an atmosphere of NH_3 gas and at a pressure ranging from about 10 Torr to about 100 Torr.

5. The method as recited in claim 4, wherein the silicon nitride layer is formed by using a source of dichlorosilane (DCS) in an atmosphere of NH_3 gas and at a pressure ranging from about 1 Torr to about 10 Torr.

6. The method as recited in claim 3, wherein the

dielectric layer is comprised of a material having one of a high dielectric constant and being a ferroelectric substance.

7. The method as recited in claim 6, wherein the material is one selected from a group of Ta_2O_5, Al_2O_3, HfO_2, $(Ba,Sr)TiO_3$ (BST), $(Pb,Zr)TiO_3$ (PZT), $(Pb,La)(Zr,Ti)O_3$ (PBZT) and Bi_4-XlaXTi_3O_{12} (BLT).